

ABSTRACT OF THE DISCLOSURE

The present invention discloses methods for manufacturing metal line of semiconductor device that can prevent undesirable etching of an edge of an interlayer insulating film. In accordance with the method, a lower metal line exposed by a via contact hole is covered by a photoresist film pattern which is formed via an exposure and development process using an upper metal line mask. An etching process is performed using the photoresist film pattern as a mask to form the upper metal line region that is then filled to form an upper metal line after removing the photoresist film pattern.